

217551US

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
YASUTAKA ITO ET AL : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW U.S. PCT APPLN :  
(Based on PCT/JP01/03759)  
FILED: HEREWITH :  
FOR: CERAMIC SUBSTRATE FOR  
SEMICONDUCTOR  
FABRICATING DEVICE

5/A  
C. 7.  
5/15/02

PRELIMINARY AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Prior to a first examination on the merits, please amend the above-identified  
application as follows:

IN THE CLAIMS

Please amend Claims 3-6 as follows:

3. (Amended) The ceramic substrate according to claim 1,  
wherein the thickness of said ceramic substrate is 25 mm or less.
4. (Amended) The ceramic substrate according to claim 1,  
wherein said conductor layer is an electrostatic electrode.
5. (Amended) The ceramic substrate according to claim 1,  
wherein said conductor layer is a resistance heating element.